

$E_g < 3.4 \text{ eV}$,

Serial No	Band Gap (E_g)	Transmittance %	Resistivity(Ωcm)	Reference
01	3.15	80	2.8×10^3	[1]
02	3.24	82	1.3×10^3	
03	3.27	81	1.2×10^2	
04	3.356	87	3.53×10^{-3}	[2]
05	3.347	84	3.51×10^{-3}	
06	3.319	82	4.38×10^{-3}	
07	3.249	93.5	9.0×10^{-3}	[3]
08	3.265	88	6.8×10^{-3}	
09	3.275	86	8.4×10^{-3}	
10	3.282	87	9.3×10^{-3}	
11	3.290	88	9.8×10^{-3}	
12	3.37	82	24.30×10^{-3}	[4]
13	3.31	81	1.50×10^{-3}	
14	3.34	80	0.80×10^{-3}	
15	3.254	82	7.256×10^{-4}	[5]
16	3.265	86	1.097×10^{-4}	
17	3.281	90	3.155×10^{-5}	
18	3.273	88	9.635×10^{-4}	

$E_g > 3.4 \text{ eV}$,

Serial No	Band Gap (E_g)	Transmittance %	Resistivity(Ωcm)	Reference
01	3.62	75	7.8×10^{-4}	[1]
02	3.454	89	2.74×10^{-3}	[2]
03	3.80	91.80	1.89×10^{-3}	[6]
04	3.65	93.26	1.03×10^{-3}	
05	3.61	91.56	5.44×10^{-3}	
06	3.55	89.55	2.29×10^{-3}	
07	3.49	93	3.50×10^{-3}	[4]
08	3.63	92	3.00×10^{-3}	
09	3.45	91	2.00×10^{-3}	
10	3.58	89.69	$1.9 \pm 0.1 \times 10^{-3}$	[7]
11	3.42	88.87	$3.9 \pm 0.003 \times 10^{-3}$	
12	3.49	89.46	$3.8 \pm 0.002 \times 10^{-3}$	
13	3.51	89.46	$3.3 \pm 0.001 \times 10^{-3}$	
14	3.52	89.61	$2.2 \pm 0.001 \times 10^{-3}$	
15	3.55	89.99	$2.4 \pm 0.001 \times 10^{-3}$	
16	3.62	92.4	2.49×10^{-3}	[8]
17	3.63	90.6	2.31×10^{-3}	
18	3.52	93.7	0.61×10^{-3}	

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